

# UTC UNISONIC TECHNOLOGIES CO., LTD

1N5406G **DIODE** 

## GLASS PASSIVATED SILICON RECTIFIER

#### **DESCRIPTION**

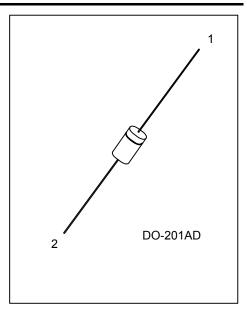
The UTC 1N5406G is a glass passivated silicon rectifier, it uses UTC's advanced technology to provide customers with high forward surge current and low reverse leakage, etc.

#### **FEATURES**

- \* Low reverse leakage
- \* High forward surge current capability

#### **SYMBOL**

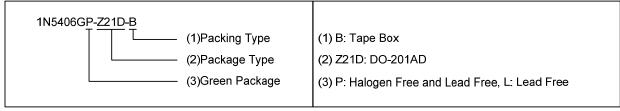




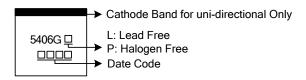
#### **ORDERING INFORMATION**

Ordering Number		Dookogo	Pin Assignment		Doolsing	
Lead Free	Halogen Free	Package	1	2	Packing	
1N5406GL-Z21D-B	1N5406GP-Z21D-B	DO-201AD	K	Α	Tape Box	

Note: Pin Assignment: A: Anode K: Cathode



#### **MARKING**



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#### ABSOLUTE MAXIMUM RATINGS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

PARAMETER	SYMBOL	RATINGS	UNIT
Working Peak Reverse Voltage	$V_{RWM}$	600	<b>&gt;</b>
Repetitive Peak Reverse Voltage	$V_{RRM}$	600	<b>&gt;</b>
RMS Voltage	$V_{RMS}$	420	<b>V</b>
DC Blocking Voltage	$V_{DC}$	600	<b>V</b>
Average Forward Rectified Current 0.375" (9.5mm) Lead Length at T <sub>A</sub> =75°C	I <sub>(AV)</sub>	3.0	Α
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load (JEDEC Method)	I <sub>FSM</sub>	200	Α
Junction Temperature	TJ	-65 ~ +175	°C
Storage Temperature	T <sub>STG</sub>	-65 ~ <b>+</b> 175	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### **■ THERMAL DATA**

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient (Note 2)	$\theta_{JA}$	20	°C/W

### **■ ELECTRICAL CHARACTERISTICS**

Ratings at 25°C ambient temperature unless otherwise specified.

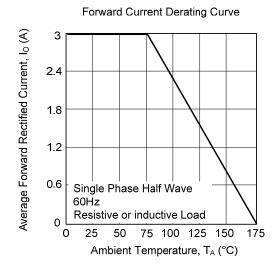
Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

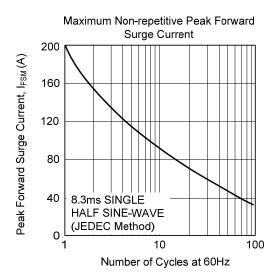
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PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Instantaneous Forward Voltage	$V_{F}$	I <sub>F</sub> =3.0A			1.2	V	
DC Reverse Current at Rated DC Blocking		T <sub>A</sub> =25°C			5.0	μΑ	
Voltage	IR	T <sub>A</sub> =100°C			100	μΑ	
Junction Capacitance (Note 1)	CJ			30.0		pF	

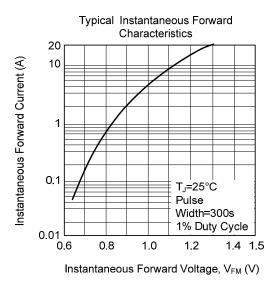
Notes: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

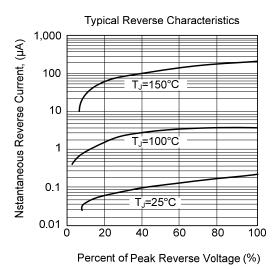
2. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted.

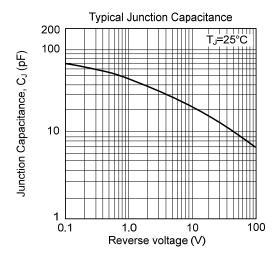
#### TYPICAL CHARACTERISTICS

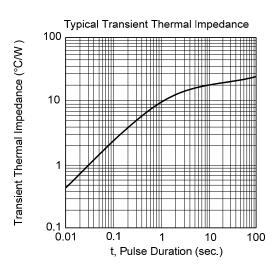












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